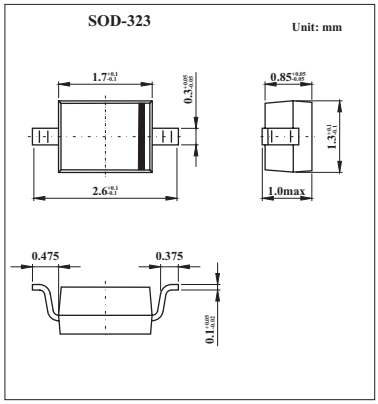
Silicon PIN Diode

BAR64-03W



Features

- High voltage current controlled RF resistor for RF attenuator and swirches
- Freqency range above 1 MHz
- Low resistance and short carrier lifetime
- For frequencies up to 3 GHz

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	200	V
Forward current	I_F	100	mA
Total Power dissipation $T_S \leqslant 25℃$	P_{tot}	250	mW
Junction temperature	T_j	150	℃
Operating temperature range	T_{op}	-55 to +150℃	℃
Storage temperature range	T_{stg}	-55 to +150℃	℃
Junction - soldering point[1)]	R_{thJA}	⩽ 450	K/W

Note:

1.Package mounted on alumina 15mm x 16.7mm x 0.7mm

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	I_R = 5 μA	200			V
Forward voltage	V_F	V_R = 20 V, f = 1 MHz			1.1	V
Diode capacitance	C_T	V_R = 0 V, f = 100 MHz		0.23	0.35	pF
Forward resistance	rf	I_F = 1 mA, f = 100 MHz		12.5	20	Ω
		I_F = 10 mA, f = 100 MHz		2.1	3.8	
		I_F = 100 mA, f = 100 MHz		0.85	1.35	
Charge carrier life time	τ_{rr}	I_F = 10 mA, I_R = 6 mA,I_R = 3mA		1.55		μs
Series inductance	Ls			2		nH

Marking

Marking	2